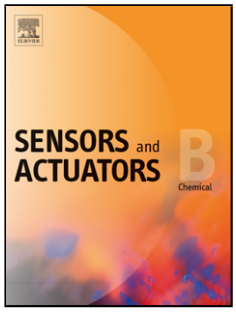

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Hydrogen sulfide detection properties of Pt-gated AlGaN/GaN HEMT-sensor

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Highlights:

- Pt-AlGaN/GaN HEMT H_2S sensors processed using micro-fabrication technology
- Sensors exhibited large signal variation and high sensitivity upon H_2S exposure
- HEMT sensors demonstrated high temperature operation capability and stability
- Excellent H_2S sensing repeatability was observed in dry air ambient at 250 °C